

Form PTO-1449 <i>O T P E</i> <i>J C 137</i>	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 99P7722US	Serial No. 09/363,523
FEB 13 2001 INFORMATION CITED BEING APPLICANT <i>PA TENT &amp; TRADEMARK OFFICE</i>		Applicant JAMMY ET AL	
(Use several sheets if necessary)		Filing Date 29-Jul-99	Group 2823

## U.S. Patent Documents

### Foreign Patent Documents

	Document Number	Date	Country	Class	Subclass	Translation
<i>ME</i>	EP 0684637	11/29/95	EP	—	—	
<i>ME</i>	EP0637063	2/1/95	EP	—	—	

Other Prior Art (including Author, Title, Date, Pertinent Pages, etc.)

ME	XP0000687427-YOSHIMARU M ET AL "HIGH QUALITY ULTRA THIN . . ." DECEMBER 13, 1992 Pgs 271-274
ME	XP000297634 THERMAL NITRIDATION OF SILICON IN A CLUSTER TOOL JANUARY 20, 1992 Pgs 341-343
ME	Yoshimaru, Inoue, Itoh, Kurogi, Tamura, Hirasita, Ichikawa and Ino, High Quality Ultra Thin $Si_3N_4$ Film Selectively Deposited on Poly-Si Electrode by LPCVD with in Situ HF Vapor Cleaning, Dec. 13, 1992, IEOM 92-271, Pgs. 271-274
ME, Examiner Michelle Estrada	Date Considered 3/26/01 Letters, Jan. 30, 1992 page 341-34